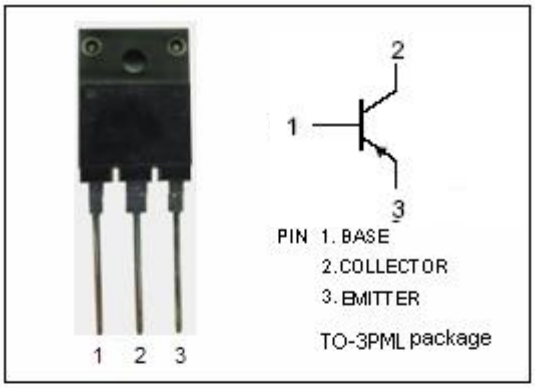
isc Silicon PNP Power Transistor — KTB778



DESCRIPTION

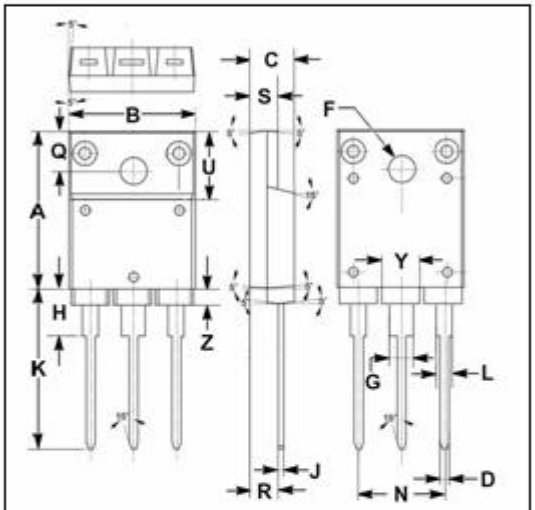
- Collector-Emitter Breakdown Voltage-
  : $V_{(BR)CEO}$= -120V(Min)
- Good Linearity of h_{FE}
- Complement to Type KTD998
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- High power amplifier applications
- Recommend for 45-50W audio frequency amplifier output stage applications

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-120	V
V_{CEO}	Collector-Emitter Voltage	-120	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-10	A
I_B	Base Current-Continuous	-1	A
P_C	Collector Power Dissipation @ T_C=25℃	80	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃



DIM	mm MIN	mm MAX
A	19.90	20.10
B	15.75	16.10
C	5.50	5.70
D	0.90	1.10
F	3.30	3.50
G	2.90	3.20
H	5.90	6.10
J	0.595	0.70
K	21.10	22.50
L	1.90	2.25
N	10.80	11.00
Q	4.90	5.10
R	3.75	3.95
S	3.20	3.60
U	9.90	10.10
Y	4.20	4.90
Z	1.90	2.10

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= -50mA ; I_B= 0	-120			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -5.0A; I_B= -0.5A			-2.5	V
$V_{BE(on)}$	Base-Emitter On Voltage	I_C= -5A ; V_{CE}= -5V			-1.5	V
I_{CBO}	Collector Cutoff Current	V_{CB}= -120V ; I_E=0			-10	μA
I_{EBO}	Emitter Cutoff Current	V_{EB}= -5V; I_C=0			-10	μA
h_{FE}	DC Current Gain	I_C= -1A ; V_{CE}= -5V	55		160	

◆ **h_{FE} Classifications**

R	O
55-110	80-160